

Complementary Silicon High-Power Transistors

2N3055AG (NPN), MJ15015G (NPN), MJ15016G (PNP)

These PowerBase complementary transistors are designed for high power audio, stepping motor and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc-to-dc converters, inverters, or for inductive loads requiring higher safe operating area than the 2N3055.

Features

- High Current-Gain – Bandwidth
- Safe Operating Area
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage 2N3055AG MJ15015G, MJ15016G	V_{CEO}	60 120	Vdc
Collector-Base Voltage 2N3055AG MJ15015G, MJ15016G	V_{CBO}	100 200	Vdc
Collector-Emitter Voltage Base Reversed Biased 2N3055AG MJ15015G, MJ15016G	V_{CEV}	100 200	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	Vdc
Collector Current – Continuous	I_C	15	Adc
Base Current	I_B	7.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ 2N3055AG MJ15015G, MJ15016G Derate above 25°C 2N3055AG MJ15015G, MJ15016G	P_D	115 180 0.65 1.03	W W W/ $^\circ\text{C}$ W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

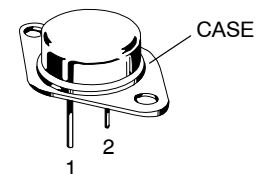
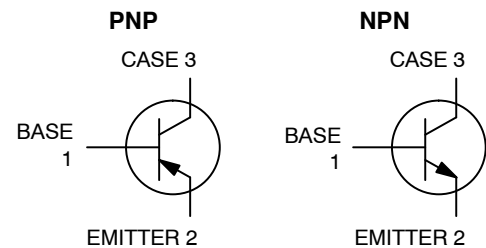
1. Indicates JEDEC Registered Data. (2N3055A)

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.52	0.98	$^\circ\text{C/W}$

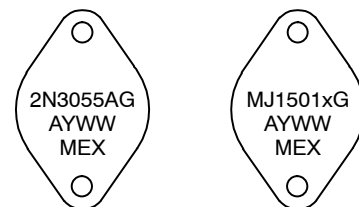
*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60, 120 VOLTS – 115, 180 WATTS



TO-204 (TO-3)
CASE 1-07
STYLE 1

MARKING DIAGRAMS



2N3055A = Device Code
MJ1501x = Device Code
x = 5 or 6
G = Pb-Free Package
A = Assembly Location
Y = Year
WW = Work Week
MEX = Country of Origin

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

2N3055AG (NPN), MJ15015G (NPN), MJ15016G (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS (Note 2)

Collector-Emitter Sustaining Voltage (Note 3) (I _C = 200 mAdc, I _B = 0)	2N3055AG MJ15015G, MJ15016G	V _{CEO(sus)}	60 120	– –	Vdc
Collector Cutoff Current (V _{CE} = 30 Vdc, V _{BE(off)} = 0 Vdc) (V _{CE} = 60 Vdc, V _{BE(off)} = 0 Vdc)	2N3055AG MJ15015G, MJ15016G	I _{CEO}	– –	0.7 0.1	mAdc
Collector Cutoff Current (Note 3) (V _{CEV} = Rated Value, V _{BE(off)} = 1.5 Vdc)	2N3055AG MJ15015G, MJ15016G	I _{CEV}	– –	5.0 1.0	mAdc
Collector Cutoff Current (V _{CEV} = Rated Value, V _{BE(off)} = 1.5 Vdc, T _C = 150°C)	2N3055AG MJ15015G, MJ15016G	I _{CEV}	– –	30 6.0	mAdc
Emitter Cutoff Current (V _{EB} = 7.0 Vdc, I _C = 0)	2N3055AG MJ15015G, MJ15016G	I _{EBO}	– –	5.0 0.2	mAdc

SECOND BREAKDOWN (Note 3)

Second Breakdown Collector Current with Base Forward Biased (t = 0.5 s non-repetitive) (V _{CE} = 60 Vdc)	2N3055AG MJ15015G, MJ15016G	I _{S/b}	1.95 3.0	– –	Adc
---	--------------------------------	------------------	-------------	--------	-----

ON CHARACTERISTICS (Note 2 and 3)

DC Current Gain (I _C = 4.0 Adc, V _{CE} = 2.0 Vdc) (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc) (I _C = 10 Adc, V _{CE} = 4.0 Vdc)		h _{FE}	10 20 5.0	70 70 –	–
Collector-Emitter Saturation Voltage (I _C = 4.0 Adc, I _B = 400 mAdc) (I _C = 10 Adc, I _B = 3.3 Adc) (I _C = 15 Adc, I _B = 7.0 Adc)		V _{CE(sat)}	– – –	1.1 3.0 5.0	Vdc
Base-Emitter On Voltage (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc)		V _{BE(on)}	0.7	1.8	Vdc

DYNAMIC CHARACTERISTICS (Note 3)

Current-Gain – Bandwidth Product (I _C = 1.0 Adc, V _{CE} = 4.0 Vdc, f = 1.0 MHz)	2N3055AG, MJ15015G MJ15016G	f _T	0.8 2.2	6.0 18	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{ob}	60	600	pF

SWITCHING CHARACTERISTICS (2N3055AG only) (Note 3)

RESISTIVE LOAD					
Delay Time	(V _{CC} = 30 Vdc, I _C = 4.0 Adc, I _{B1} = I _{B2} = 0.4 Adc, t _p = 25 μs Duty Cycle ≤ 2%)	t _d	–	0.5	μs
Rise Time		t _r	–	4.0	μs
Storage Time		t _s	–	3.0	μs
Fall Time		t _f	–	6.0	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

3. Indicates JEDEC Registered Data. (2N3055A)

2N3055AG (NPN), MJ15015G (NPN), MJ15016G (PNP)

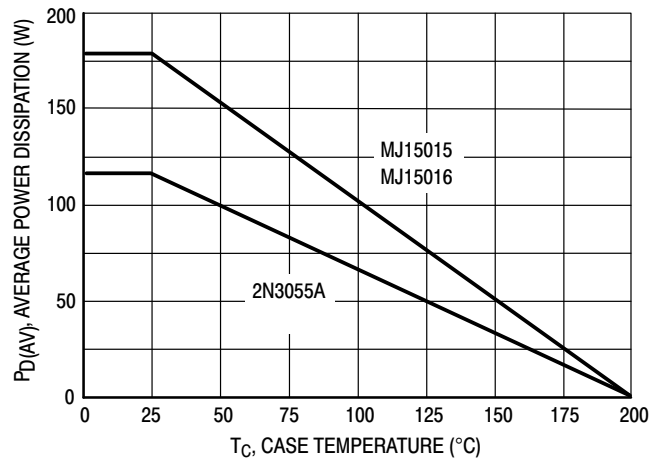


Figure 1. Power Derating

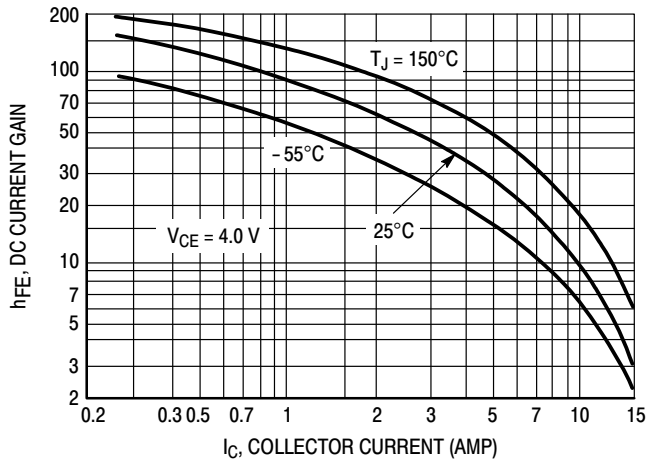


Figure 2. DC Current Gain

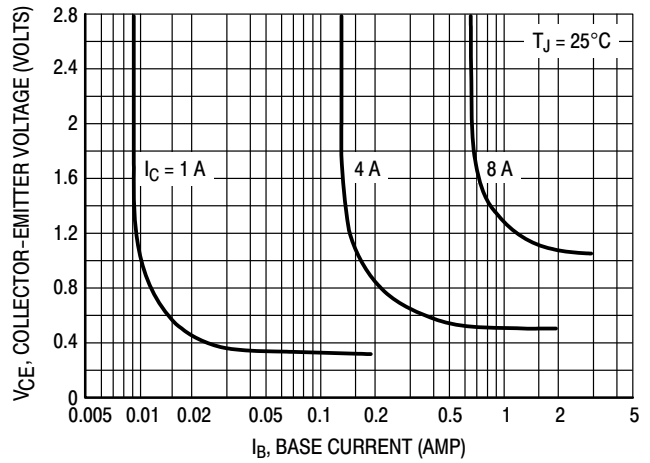


Figure 3. Collector Saturation Region

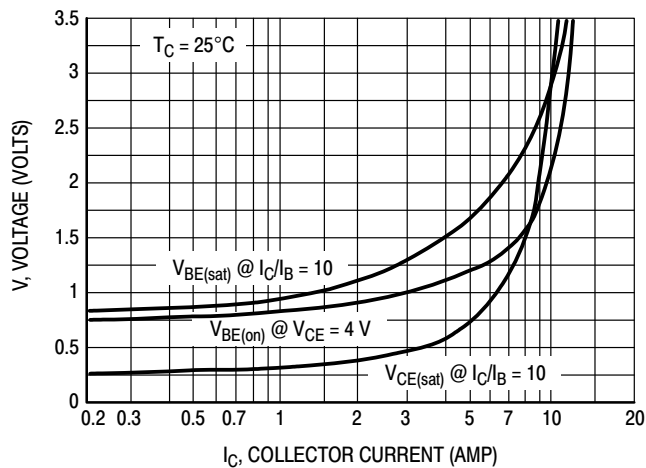


Figure 4. "On" Voltages

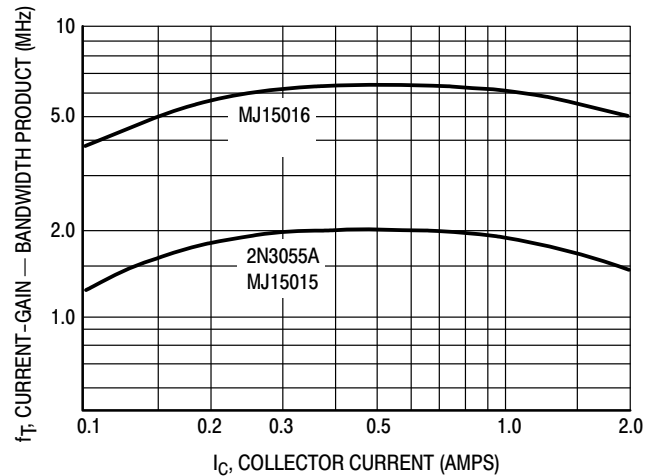


Figure 5. Current-Gain - Bandwidth Product

2N3055AG (NPN), MJ15015G (NPN), MJ15016G (PNP)

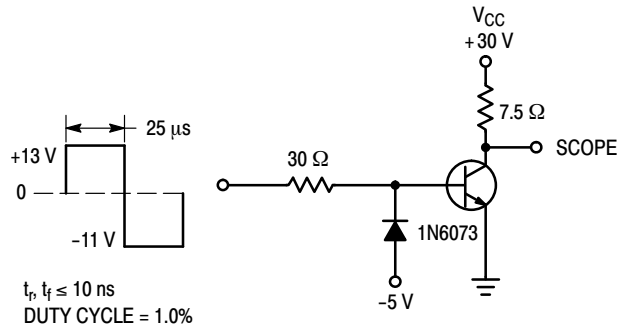


Figure 6. Switching Times Test Circuit
(Circuit shown is for NPN)

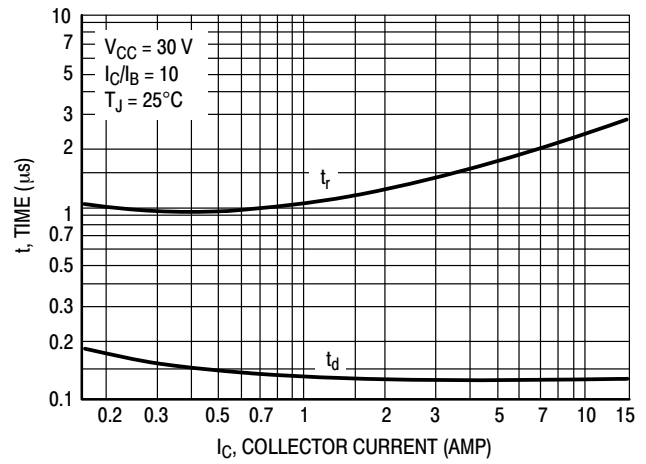


Figure 7. Turn-On Time

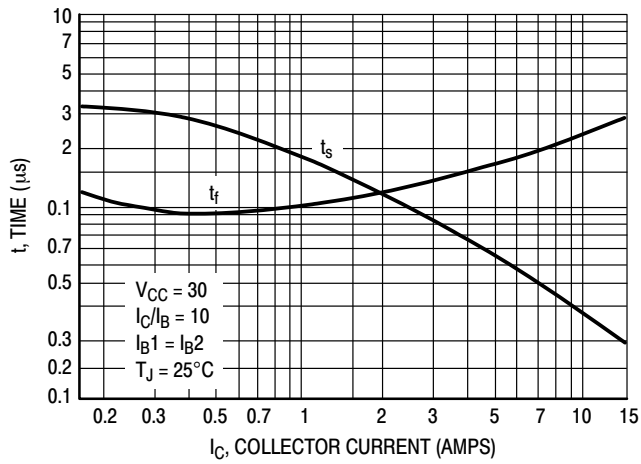


Figure 8. Turn-Off Times

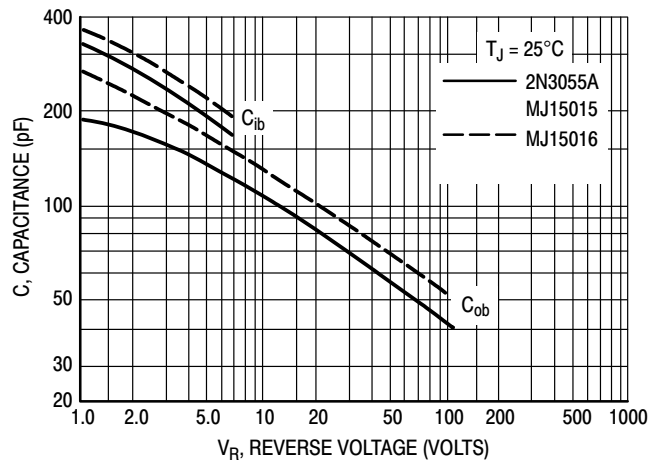


Figure 9. Capacitances

2N3055AG (NPN), MJ15015G (NPN), MJ15016G (PNP)

COLLECTOR CUT-OFF REGION

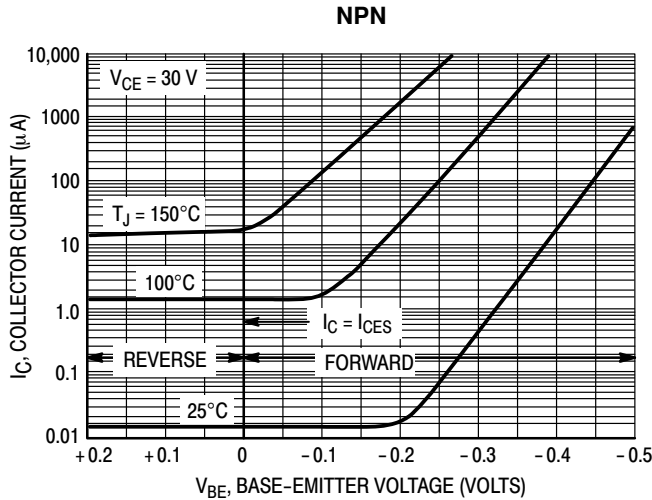


Figure 10. 2N3055A, MJ15015

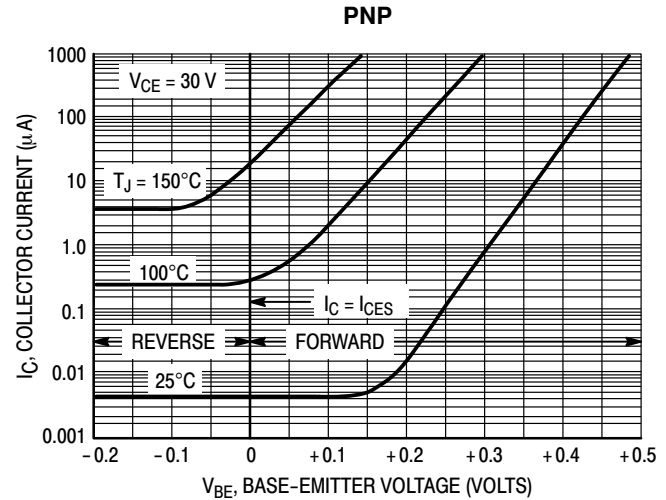


Figure 11. MJ15016

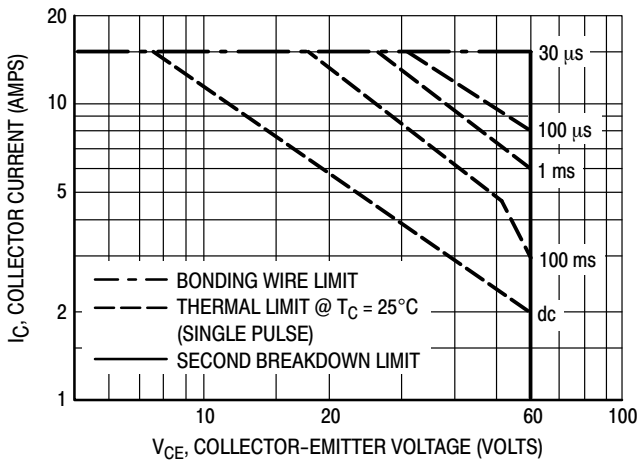


Figure 12. Forward Bias Safe Operating Area
2N3055A

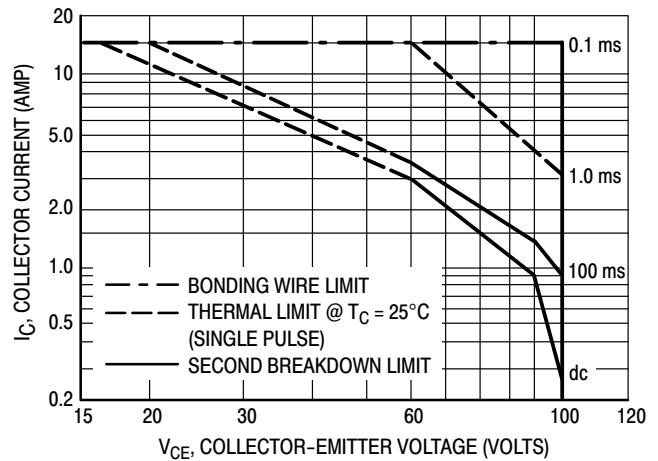


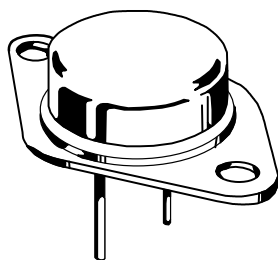
Figure 13. Forward Bias Safe Operating Area
MJ15015, MJ15016

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe Operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 12 and 13 is based on $T_C = 25^\circ\text{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

ORDERING INFORMATION

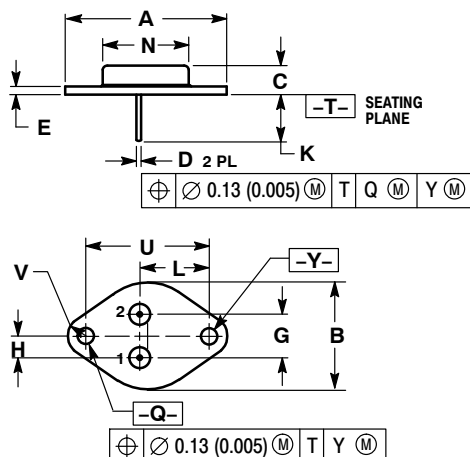
Device	Package	Shipping
2N3055AG	TO-204 (Pb-Free)	100 Units / Tray
MJ15015G	TO-204 (Pb-Free)	100 Units / Tray
MJ15016G	TO-204 (Pb-Free)	100 Units / Tray



TO-204 (TO-3)
CASE 1-07
ISSUE Z

DATE 10 MAR 2000

SCALE 1:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

STYLE 2:
PIN 1. BASE
2. COLLECTOR
CASE: EMITTER

STYLE 3:
PIN 1. GATE
2. SOURCE
CASE: DRAIN

STYLE 4:
PIN 1. GROUND
2. INPUT
CASE: OUTPUT

STYLE 5:
PIN 1. CATHODE
2. EXTERNAL TRIP/DELAY
CASE: ANODE

STYLE 6:
PIN 1. GATE
2. EMITTER
CASE: COLLECTOR

STYLE 7:
PIN 1. ANODE
2. OPEN
CASE: CATHODE

STYLE 8:
PIN 1. CATHODE #1
2. CATHODE #2
CASE: ANODE

STYLE 9:
PIN 1. ANODE #1
2. ANODE #2
CASE: CATHODE

DOCUMENT NUMBER:	98ASB42001B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-204 (TO-3)	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales